

Amendments to the Specification:

Please amend paragraph [0002] as follows:

Hetero-junction bipolar transistors (HBTs) have been developed for high frequency power amplification systems such as mobile telephones and other mobile communication devices. While an HBT, like other transistors, includes an emitter, base, and collector, unlike conventional homojunction transistors (for example typical Si bipolar junction transistors) at least one of the emitter, base, and collector of an HBT are not formed of materials having the same bandgap. In single HBTs, the emitter and base materials are different to increase the flow of charged carriers (and thus current) in the desired direction between the emitter and base and decrease the flow of charged carriers of the opposite type in the reverse direction. A schematic of a general transistor structure is shown in Fig. 5, which shows the transistor 500, an emitter 502, a base 504, and a collector 506 as well as leads 510 from contact layers 508 on these respective portions of the transistor 500. In bipolar junction transistors, n-p-n transistors are formed using an emitter and collector doped with impurities that provide extra electrons and a base doped with impurities that provide extra holes.